

SINGLE AND DUAL TVS FOR ESD / TRANSIENT PROTECTION

This Single and Dual Transient Protector has been designed to protect Sensitive Equipment against ESD and prevent Latch-Up events. The single unidirectional and the dual used as bi-directional devices protect up to two data lines in a single package giving the advantage of board space savings where this is a premium.

SPECIFICATION FEATURES

- Working Peak Reverse Voltage Range - 5 to 24V
- Maximum Leakage Current of 5 μ A
- IEC61000-4-2 Compliance 15kV Air, 8kV Contact Discharge
- Industry Standard SOT23 Package

APPLICATIONS

- Data Transmission Line Ports
- Computer Monitor Interface Port Protection
- Portable Consumer Electronics
- Instrumentation Equipment

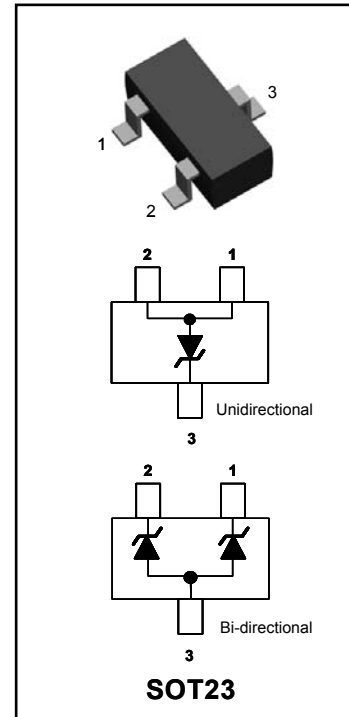
MAXIMUM RATINGS

Rating	Symbol	Value	Units
Peak Pulse Power 8/20 μ s Waveform	P_{ppm}	500	W
ESD Voltage (HBM)	V_{ESD}	>25	kV
Operating Temperature Range	T_J	-55 to +150	$^{\circ}$ C
Storage Temperature Range	T_{stg}	-55 to +150	$^{\circ}$ C
Lead Soldering Temperature (max 10 secs)	T_L	260	$^{\circ}$ C

ELECTRICAL CHARACTERISTICS $T_j = 25^{\circ}$ C

PJSOT05, PJSOT05C (Bi-directional)

Parameter	Symbol	Conditions	Min	Typical	Max	Units
Reverse Stand-Off Voltage	V_{WRM}				5	V
Reverse Breakdown Voltage	V_{BR}	$I_{BR} = 1mA$	6			V
Reverse Leakage Current	I_R	$V_R = 5V$			5	μ A
Clamping Voltage (820 μ s)	V_C	$I_{pp} = 20A$			10	V
Maximum Peak Pulse Current	I_{pp}	8/20 μ s Waveform			30	A
Off State Capacitance (Unidirectional)	C_j	0 Vdc Bias f = 1MHz			550	pF
Off State Capacitance (Bi-directional)	C_j	0 Vdc Bias f = 1MHz between pin 1 and 2			220	pF





ELECTRICAL CHARACTERISTICS $T_j = 25^\circ\text{C}$

PJSOT12, PJSOT12C (Bi-directional)

Parameter	Symbol	Conditions	Min	Typical	Max	Units
Reverse Stand-Off Voltage	V_{WRM}				12	V
Reverse Breakdown Voltage	V_{BR}	$I_{BR} = 1\text{mA}$	13.3			V
Reverse Leakage Current	I_R	$V_R = 12\text{V}$			5	μA
Clamping Voltage (820 μs)	V_C	$I_{pp} = 20\text{A}$			25	V
Maximum Peak Pulse Current	I_{pp}	8/20 μs Waveform			24	A
Off State Capacitance (Unidirectional)	C_j	0 Vdc Bias $f = 1\text{MHz}$			200	pF
Off State Capacitance (Bi-directional)	C_j	0 Vdc Bias $f = 1\text{MHz}$ between pin 1 and 2			100	pF

PJSOT15, PJSOT15C (Bi-directional)

Parameter	Symbol	Conditions	Min	Typical	Max	Units
Reverse Stand-Off Voltage	V_{WRM}				15	V
Reverse Breakdown Voltage	V_{BR}	$I_{BR} = 1\text{mA}$	16.7			V
Reverse Leakage Current	I_R	$V_R = 15\text{V}$			5	μA
Clamping Voltage (8/20 μs)	V_C	$I_{pp} = 20\text{A}$			30	V
Maximum Peak Pulse Current	I_{pp}	8/20 μs Waveform			20	A
Off State Capacitance (Unidirectional)	C_j	0 Vdc Bias $f = 1\text{MHz}$			170	pF
Off State Capacitance (Bi-directional)	C_j	0 Vdc Bias $f = 1\text{MHz}$ between pin 1 and 2			85	pF

PJSOT24, PJSOT24C (Bi-directional)

Parameter	Symbol	Conditions	Min	Typical	Max	Units
Reverse Stand-Off Voltage	V_{WRM}				24	V
Reverse Breakdown Voltage	V_{BR}	$I_{BR} = 1\text{mA}$	26.7			V
Reverse Leakage Current	I_R	$V_R = 24\text{V}$			5	μA
Clamping Voltage (8/20 μs)	V_C	$I_{pp} = 15\text{A}$			45	V
Maximum Peak Pulse Current	I_{pp}	8/20 μs Waveform			18	A
Off State Capacitance (Unidirectional)	C_j	0 Vdc Bias $f = 1\text{MHz}$			150	pF
Off State Capacitance (Bi-directional)	C_j	0 Vdc Bias $f = 1\text{MHz}$ between pin 1 and 2			75	pF

PRELIMINARY

PACKAGE LAYOUT DIMENSIONS AND PAD LAYOUT

PRELIMINARY

